



MiniSKiIP[®] 0

1-phase bridge rectifier +
3-phase bridge inverter

SKiIP 01NEC066V3

Features

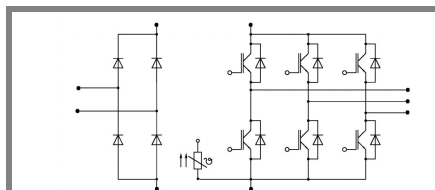
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 3,5 kVA
- Typical motor power 1,5 kW

Remarks

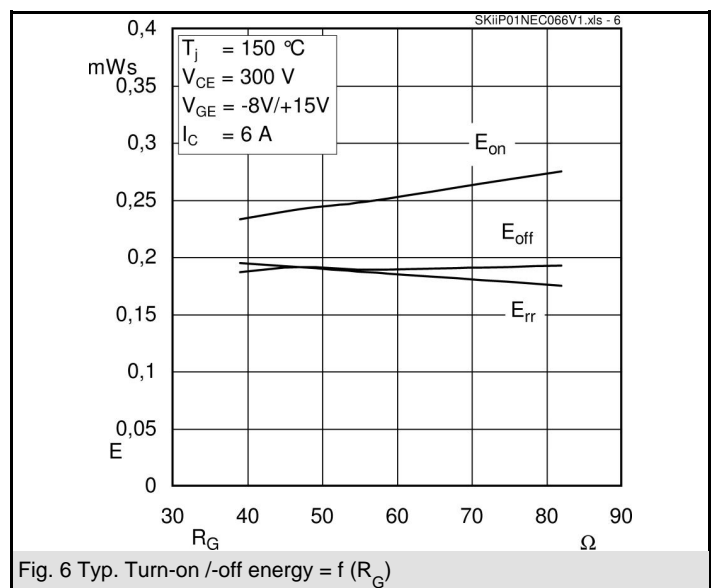
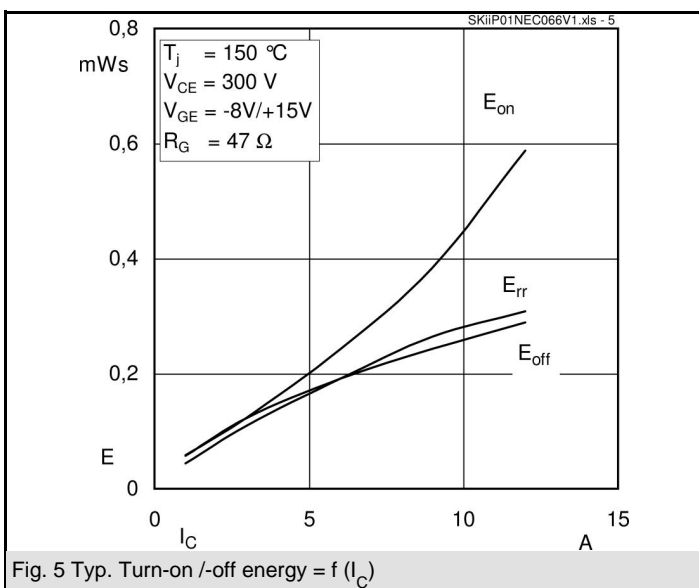
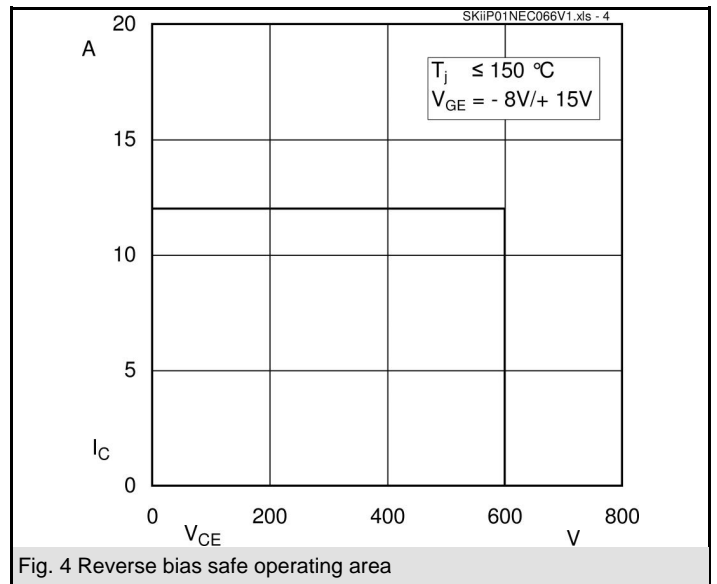
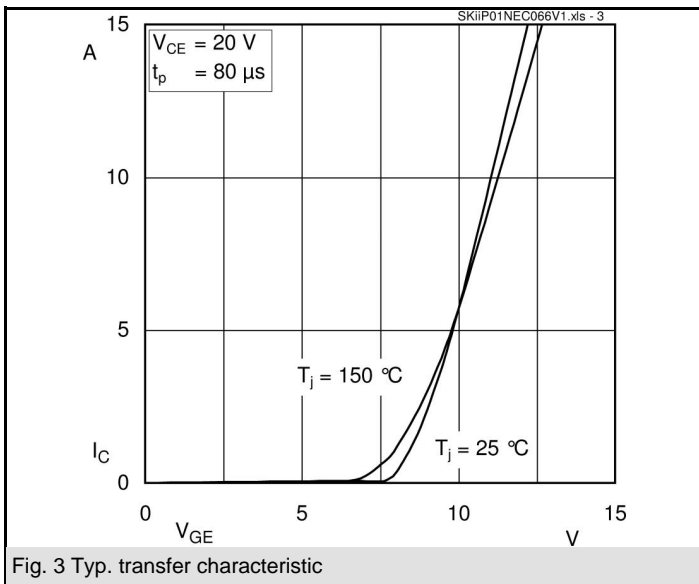
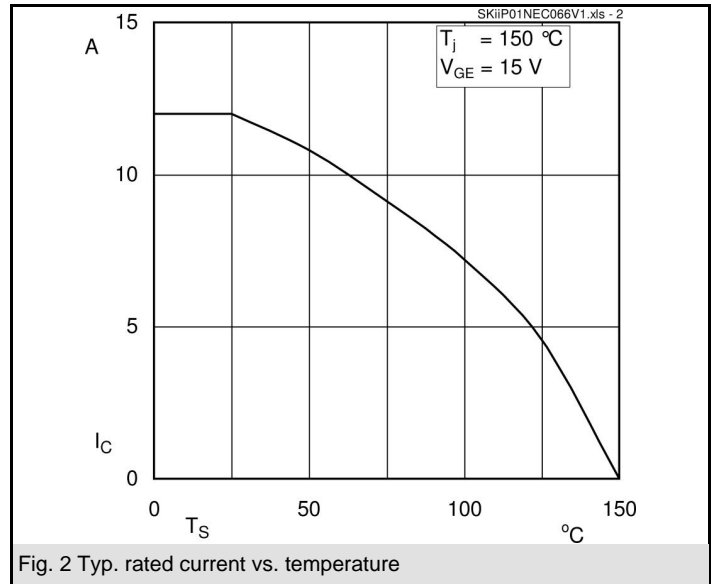
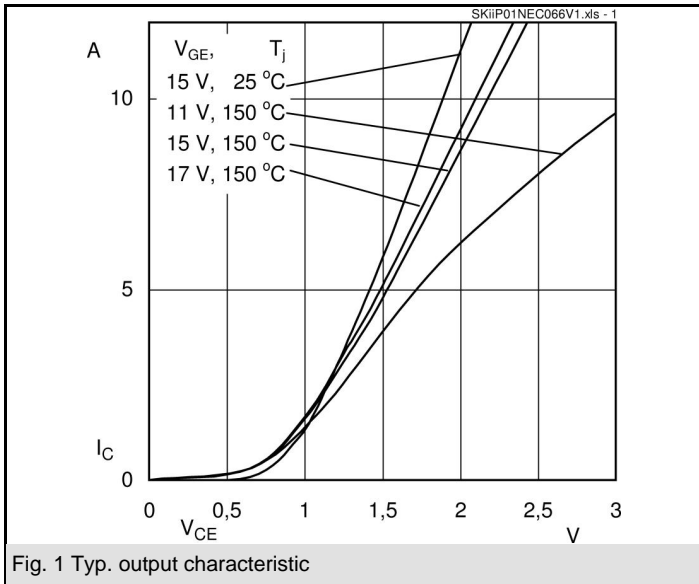
- Case temperature limited to $T_C = 125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j = 150^\circ\text{C}$
- SC data: $t_p \leq 6 \mu\text{s}$; $V_{GE} \leq 15 \text{ V}$; $T_j = 150^\circ\text{C}$; $V_{CC} = 360 \text{ V}$
- V_{CEsat} , $V_F =$ chip level value



NEC

| Absolute Maximum Ratings | | $T_s = 25^\circ\text{C}$, unless otherwise specified | |
|--------------------------|---|---|----------------------|
| Symbol | Conditions | Values | Units |
| IGBT - Inverter | | | |
| V_{CES} | | 600 | V |
| I_C | $T_s = 25 (70)^\circ\text{C}$, $T_j = 150^\circ\text{C}$ | 12 (11) | A |
| I_C | $T_s = 25 (70)^\circ\text{C}$, $T_j = 175^\circ\text{C}$ | 12 (12) | A |
| I_{CRM} | $t_p = 1 \text{ ms}$ | 12 | A |
| V_{GES} | | ± 20 | V |
| Diode - Inverter | | | |
| I_F | $T_s = 25 (70)^\circ\text{C}$, $T_j = 150^\circ\text{C}$ | 12 (12) | A |
| I_F | $T_s = 25 (70)^\circ\text{C}$, $T_j = 175^\circ\text{C}$ | 12 (12) | A |
| I_{FRM} | $t_p = 1 \text{ ms}$ | 12 | A |
| Diode - Rectifier | | | |
| V_{RRM} | | 800 | V |
| I_F | $T_s = 70^\circ\text{C}$ | 35 | A |
| I_{FSM} | $t_p = 10 \text{ ms}$, $\sin 180^\circ$, $T_j = 25^\circ\text{C}$ | 220 | A |
| i^2t | $t_p = 10 \text{ ms}$, $\sin 180^\circ$, $T_j = 25^\circ\text{C}$ | 240 | A^2s |
| I_{tRMS} | per power terminal (20 A / spring) | 20 | A |
| T_j | IGBT, Diode | -40...+175 | $^\circ\text{C}$ |
| T_{stg} | | -40...+125 | $^\circ\text{C}$ |
| V_{isol} | AC, 1 min. | 2500 | V |

| Characteristics | | $T_s = 25^\circ\text{C}$, unless otherwise specified | | | Units |
|---------------------------|---|---|-------------|-------------|------------------|
| Symbol | Conditions | min. | typ. | max. | Units |
| IGBT - Inverter | | | | | |
| $V_{CE(sat)}$ | $I_{Cnom} = 6 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$ | 1,1 | 1,45 (1,65) | 1,85 (2,05) | V |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}$, $I_C = 1 \text{ mA}$ | | 5,8 | | V |
| $V_{CE(TO)}$ | $T_j = 25 (150)^\circ\text{C}$ | | 0,9 (0,7) | 1,1 (1) | V |
| r_{CE} | $T_j = 25 (150)^\circ\text{C}$ | | 100 (167) | 134 (184) | $\text{m}\Omega$ |
| C_{ies} | $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | | 0,45 | | nF |
| C_{oes} | $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | | 0,1 | | nF |
| C_{res} | $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$ | | 0,05 | | nF |
| $R_{CC+EE'}$ | spring contact-chip $T_s = 25 (150)^\circ\text{C}$ | | | | $\text{m}\Omega$ |
| $R_{th(j-s)}$ | per IGBT | | 2,4 | | K/W |
| $t_{d(on)}$ | under following conditions | | 20 | | ns |
| t_r | $V_{CC} = 300 \text{ V}$, $V_{GE} = -8\text{V}/+15\text{V}$ | | 25 | | ns |
| $t_{d(off)}$ | $I_{Cnom} = 6 \text{ A}$, $T_j = 150^\circ\text{C}$ | | 175 | | ns |
| t_f | $R_{Gon} = R_{Goff} = 47 \Omega$ | | 60 | | ns |
| $E_{on} (E_{off})$ | inductive load | | 0,3 (0,2) | | mJ |
| Diode - Inverter | | | | | |
| $V_F = V_{EC}$ | $I_F = 6 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$ | | 1,3 (1,3) | 1,6 (1,6) | V |
| $V_{(TO)}$ | $T_j = 25 (150)^\circ\text{C}$ | | 0,9 (0,8) | 1 (0,9) | V |
| r_T | $T_j = 25 (150)^\circ\text{C}$ | | 67 (83) | 100 (117) | $\text{m}\Omega$ |
| $R_{th(j-s)}$ | per diode | | 3 | | K/W |
| I_{RRM} | under following conditions | | 11,2 | | A |
| Q_{rr} | $I_{Fnom} = 6 \text{ A}$, $V_R = 300 \text{ V}$ | | 0,9 | | μC |
| E_{rr} | $V_{GE} = 0 \text{ V}$, $T_j = 150^\circ\text{C}$ $di_F/dt = 520 \text{ A}/\mu\text{s}$ | | 0,2 | | mJ |
| Diode - Rectifier | | | | | |
| V_F | $I_{Fnom} = 15 \text{ A}$, $T_j = 25^\circ\text{C}$ | | 1,1 | | V |
| $V_{(TO)}$ | $T_j = 150^\circ\text{C}$ | | 0,8 | | V |
| r_T | $T_j = 150^\circ\text{C}$ | | 20 | | $\text{m}\Omega$ |
| $R_{th(j-s)}$ | per diode | | 1,5 | | K/W |
| Temperature Sensor | | | | | |
| R_{ts} | 3 %, $T_r = 25 (100)^\circ\text{C}$ | | 1000(1670) | | Ω |
| Mechanical Data | | | | | |
| w | | | 21,5 | | g |
| M_s | Mounting torque | 2 | | 2,5 | Nm |



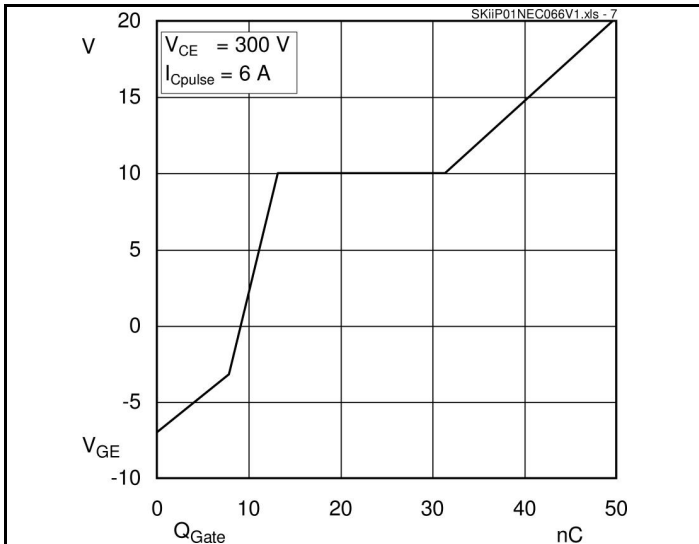


Fig. 7 Typ. gate charge characteristic

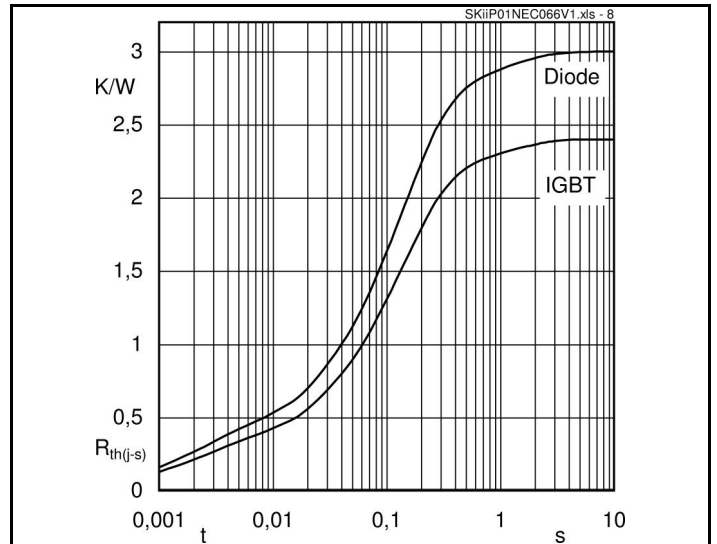


Fig. 8 Typ. thermal impedance

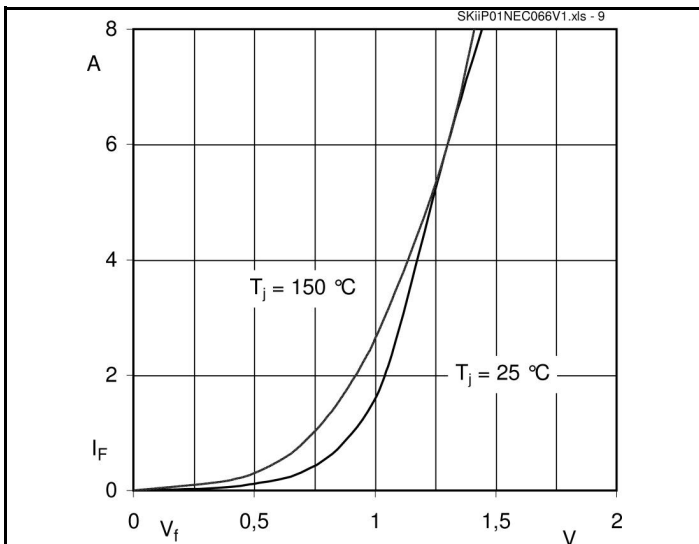


Fig. 9 Typ. freewheeling diode forward characteristic

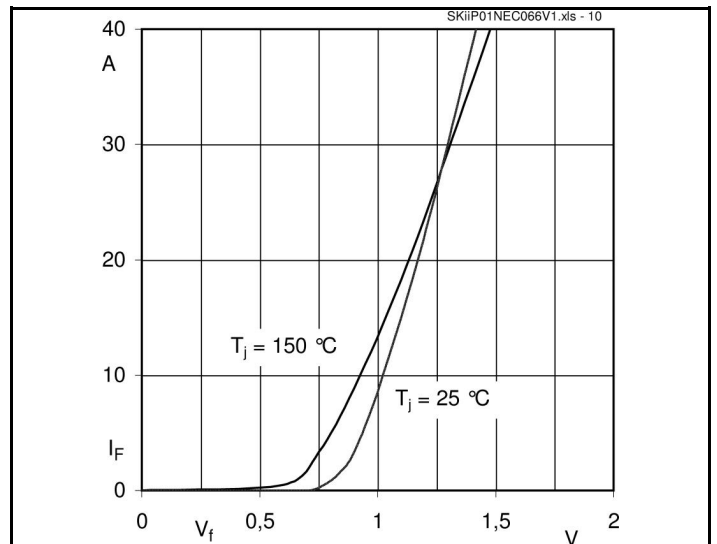
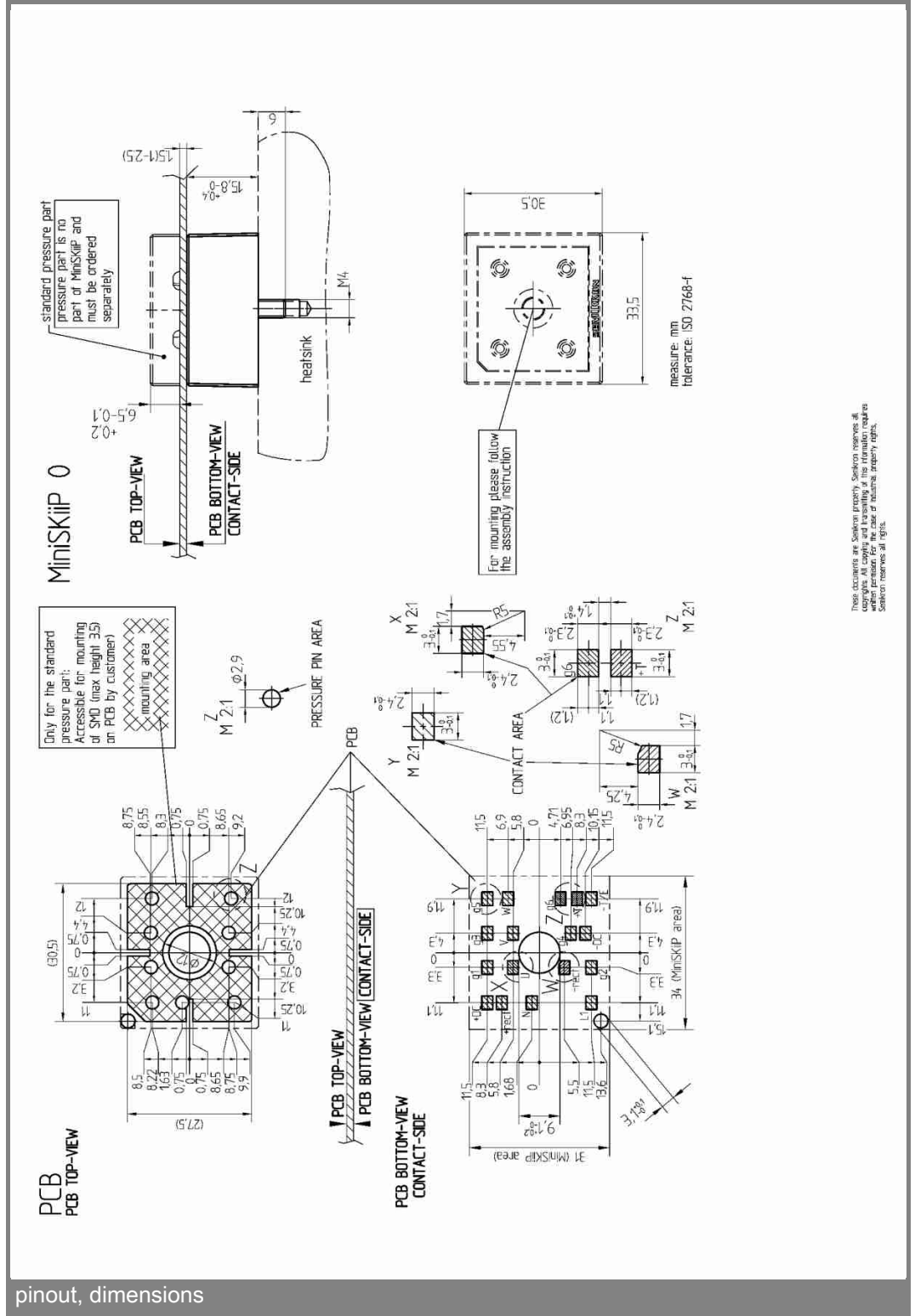
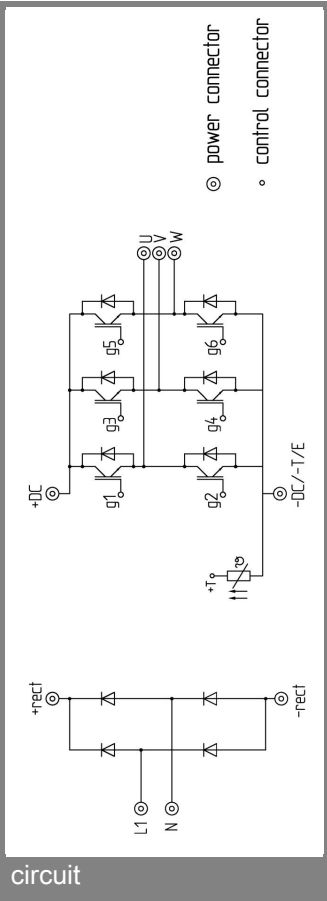


Fig. 10 Typ. input bridge forward characteristic



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.